



Shantou Huashan Electronic Devices Co.,Ltd.

NPN DIGITAL TRANSISTOR

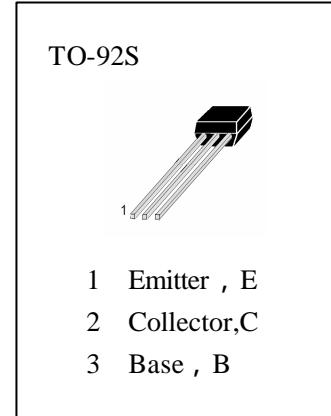
HC143X

APPLICATIONS

Switching Circuit , Interface Circuit.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature..... -55~150
 T_j —Junction Temperature..... 150
 P_c —Collector Dissipation..... 300mW
 V_{CBO} —Collector-Base Voltage..... 50V
 V_{CEO} —Collector-Emitter Voltage..... 50V
 V_{EBO} —Emitter-Base Voltage..... 5V
 I_c —Collector Current..... 100mA



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	50			V	$I_C=10 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	50			V	$I_C=0.1mA, I_B=0$
ICBO	Collector Cut-off Current			0.1	μA	$V_{CB}=40V, I_E=0$
ICEO	Collector Cut-off Current			0.5	μA	$V_{CE}=40V, I_B=0$
IEBO	Emitter Cut-off Current	200	340	420	μA	$V_{EB}=5V, I_C=0$
HFE	DC Current Gain	30				$V_{CE}=5V, I_C=1mA$
VCE(sat)	Collector- Emitter Saturation Voltage		0.1	0.3	V	$I_C=10mA, I_B=0.5mA$
VI (off)	Input Off Voltage	0.3			V	$V_{CE}=5V, I_C=0.1mA$
VI (on)	Input On Voltage			2.5	V	$V_{CE}=0.3V, I_C=20mA$
R1	Input Resistor	3.2	4.7	6.2	Kohm	
R1/R2	Resistance Ratio	0.42	0.47	0.52		
fr	Current Gain-Bandwidth Product		250		MHz	$V_{CE}=10V, I_C=5mA$